

Accompanying this amendment is a copy of an article by F. Goodenough, "Dense MOSFET Enables Portable Power Control," *Electronic Design*, April 14, 1997, pages 45, 46, 48-50 (intervening ad omitted). This article is not prior art but provides an independent description of the structure and operation of the power MOSFET of Bulucea et al. U.S. Pat. No. 5,298,442, cited in the parent case. The structure with protecting diode is shown in perspective section in FIG. 5, page 49. Page 50 states "Despite its benefit, use of the protecting diode is problematic since it limits the maximum cell density because it takes up cell area, that is, it makes the cells bigger cutting density."

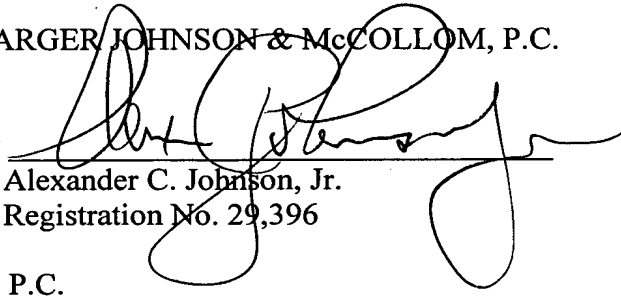
The structure recited in claim 34--i.e., the second doping concentration contained within the body layer and contacting the source conductor at the bottom of the second trench (see Pt portion of P body in FIG. 13)--achieves these benefits without taking up cell area, that is, without making the cells bigger, and thereby enabling greater cell density. Therefore, the claims should be allowable.

No new matter is added.

Respectfully submitted,

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